



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

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2SK3372G

Silicon N-Channel Junction FET

For impedance conversion in low frequency

For electret capacitor microphone

■ Features

- High mutual conductance g_m
- Low noise voltage NV

■ Package

- Code
SSSMINI3-F2

• Pin Name

- 1: Drain
- 2: Source
- 3: Gate

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Drain-source voltage (Gate open)	V_{DSO}	20	V
Gate-drain voltage (Source open)	V_{GDO}	20	V
Drain-source current (Gate open)	I_{DSO}	2	mA
Gate-drain current (Source open)	I_{GDO}	2	mA
Gate-source current (Drain open)	I_{GSO}	2	mA
Power dissipation	P_D	100	mW
Operating ambient temperature	T_{opr}	-20 to +80	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +125	$^\circ\text{C}$

■ Marking Symbol: 1H

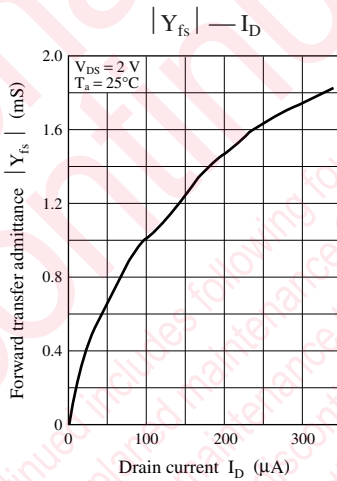
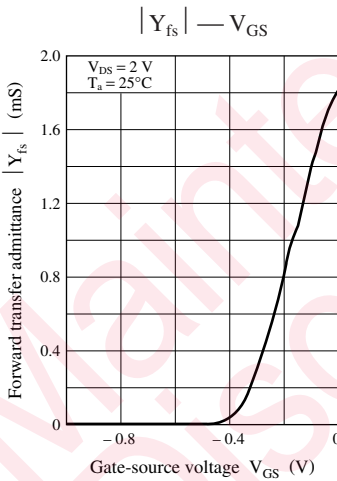
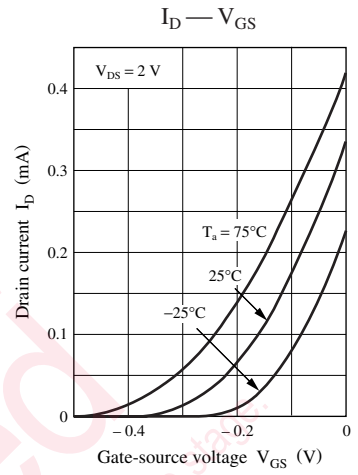
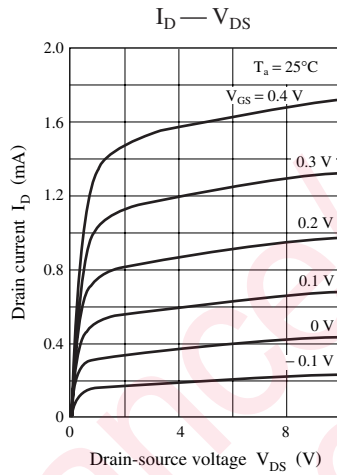
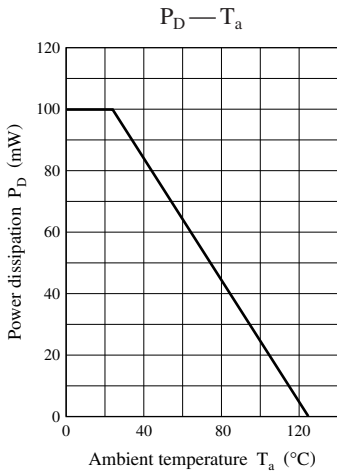
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain current *1	I_D	$V_{DS} = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$	100		470	μA
Drain-source current	I_{DSS}	$V_{DS} = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$, $V_{GS} = 0$	107		460	μA
Mutual conductance	g_m	$V_D = 2.0\text{ V}$, $V_{GS} = 0$, $f = 1\text{ kHz}$	660	1600		μS
Noise voltage	NV	$V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, A-Curve			4	μV
Voltage gain	G_{V1}	$V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$	-7.5	-4.7		dB
	G_{V2}	$V_D = 12\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$	-4.0	-1.5		
	G_{V3}	$V_D = 1.5\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$	-8.0	-5.0		
	$\Delta G_V \cdot f $ *2	$V_D = 2.0\text{ V}$, $R_D = 2.2\text{ k}\Omega \pm 1\%$ $C_O = 5\text{ pF}$, $e_G = 10\text{ mV}$, $f = 1\text{ kHz}$ to 70 Hz		0	1.7	
Voltage gain difference	$ G_{V2} - G_{V1} $		0		4.0	dB
	$ G_{V1} - G_{V3} $		0		1.7	

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

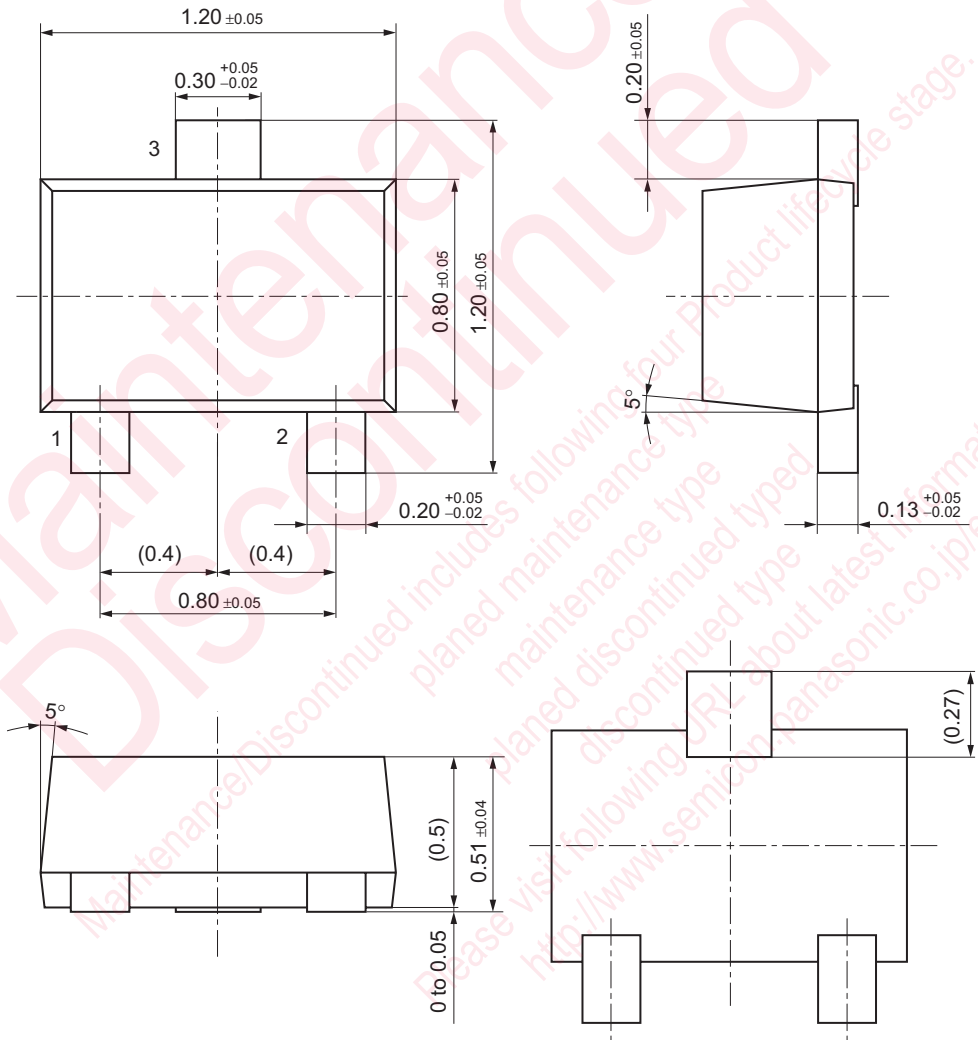
2. *1: I_D is assured for I_{DSS} .

*2: $\Delta |G_V \cdot f|$ is assured for AQL 0.065%. (The measurement method is used by source-grounded circuit.)



SSSMini3-F2

Unit: mm



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